

## AOI7S65-VB Datasheet

### N-Channel 650V (D-S) Super Junction Power MOSFET



**RoHS**  
 COMPLIANT  
 HALOGEN  
**FREE**

PRODUCT SUMMARY		
$V_{DS}$ (V) at $T_J$ max.	650	
$R_{DS(on)}$ typ. ( $\Omega$ ) at 25 °C	$V_{GS} = 10$ V	0.550

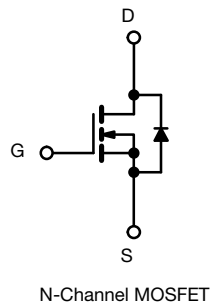
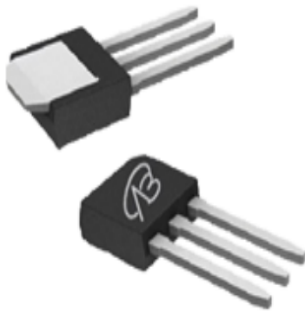
#### FEATURES

- Low figure-of-merit (FOM)  $R_{on} \times Q_g$
- Low input capacitance ( $C_{iss}$ )
- Reduced switching and conduction losses
- Ultra low gate charge ( $Q_g$ )
- Avalanche energy rated (UIS)

#### APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial
  - Welding
  - Induction heating
  - Motor drives
  - Battery chargers
  - Renewable energy
  - Solar (PV inverters)

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


ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	650	V
Gate-source voltage	$V_{GS}$	$\pm 30$	
Continuous drain current ( $T_J = 150$ °C)	$V_{GS}$ at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed drain current <sup>a</sup>	$I_{DM}$	24	
Linear derating factor		1.7	W/°C
Single pulse avalanche energy <sup>b</sup>	$E_{AS}$	185	mJ
Maximum power dissipation	$P_D$	128	W
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	°C
Drain-source voltage slope	$dV/dt$	$T_J = 125$ °C	V/ns
Reverse diode $dV/dt$ <sup>d</sup>			
Soldering recommendations (peak temperature) <sup>c</sup>	For 10 s	260	°C

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 100$  V, starting  $T_J = 25$  °C,  $L = 30$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 8.0$  A
- 1.6 mm from case
- $I_{SD} \leq I_D$ ,  $dI/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	-	62	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	-	0.65	

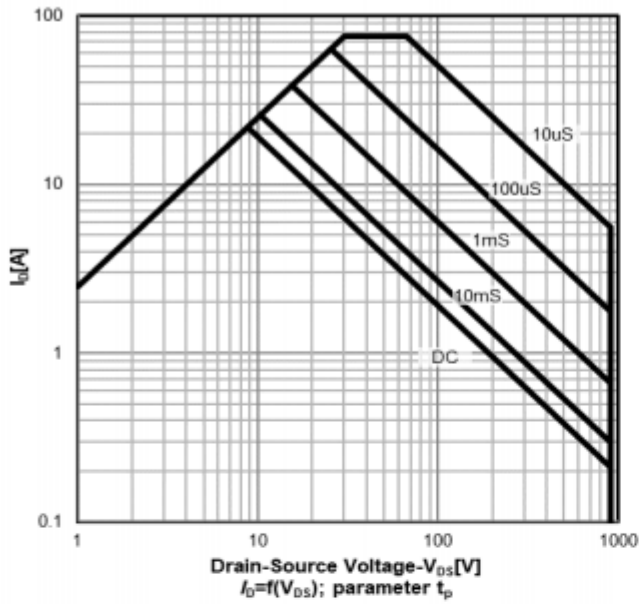
SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		650	-	-	V
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$		-	1.08	-	V/°C
Gate-source threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-source leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
		$V_{GS} = \pm 30\text{ V}$		-	-	$\pm 1$	$\mu\text{A}$
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$		-	-	1	$\mu\text{A}$
		$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	10	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 2.5\text{ A}$	-	0.550	-	$\Omega$
Forward transconductance	$g_{fs}$	$V_{DS} = 30\text{ V}, I_D = 2.5\text{ A}$		-	8.7	-	S
<b>Dynamic</b>							
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$		-	2600	-	pF
Output capacitance	$C_{oss}$			-	81	-	
Reverse transfer capacitance	$C_{rss}$			-	9	-	
Effective output capacitance, energy related <sup>a</sup>	$C_{o(er)}$			-	58	-	
Effective output capacitance, time related <sup>b</sup>	$C_{o(tr)}$	$V_{DS} = 0\text{ V to } 480\text{ V}, V_{GS} = 0\text{ V}$		-	296	-	
Total gate charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 5\text{ A}, V_{DS} = 480\text{ V}$	-	40	122	nC
Gate-source charge	$Q_{gs}$			-	16	-	
Gate-drain charge	$Q_{gd}$			-	20	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 480\text{ V}, I_D = 5\text{ A}, V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$		-	22	44	ns
Rise time	$t_r$			-	24	48	
Turn-off delay time	$t_{d(off)}$			-	71	142	
Fall time	$t_f$			-	26	52	
Gate input resistance	$R_g$			$f = 1\text{ MHz}, \text{open drain}$		0.3	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous source-drain diode current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	8	A
Pulsed diode forward current	$I_{SM}$			-	-	24	
Diode forward voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 5\text{ A}, V_{GS} = 0\text{ V}$		-	-	1.2	V
Reverse recovery time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 5\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, V_R = 25\text{ V}$		-	66	132	ns
Reverse recovery charge	$Q_{rr}$			-	6.4	12.8	$\mu\text{C}$
Reverse recovery current	$I_{RRM}$			-	27	-	A

**Notes**

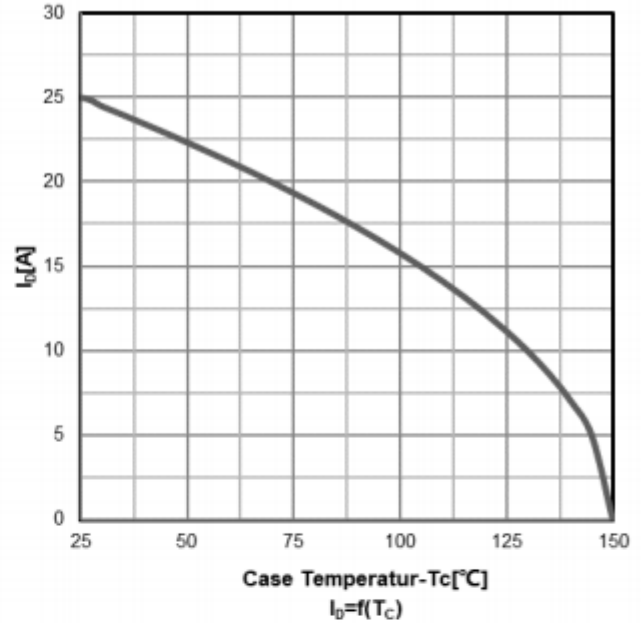
- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$   
 b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

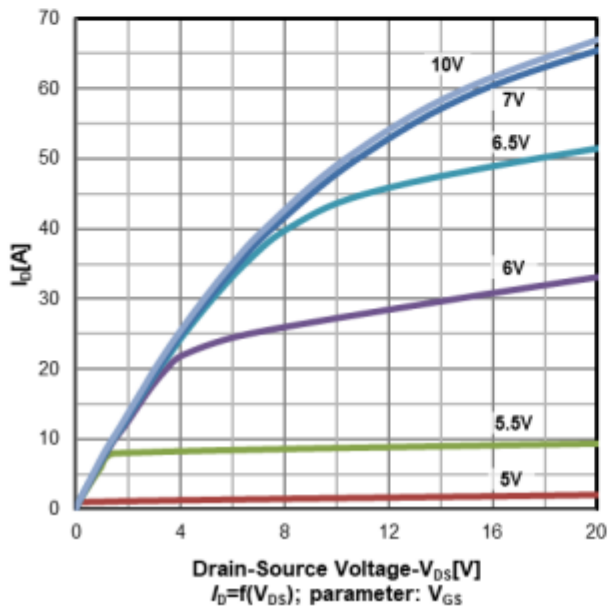
Safe operating area TC=25 °C  
Non FullPAK



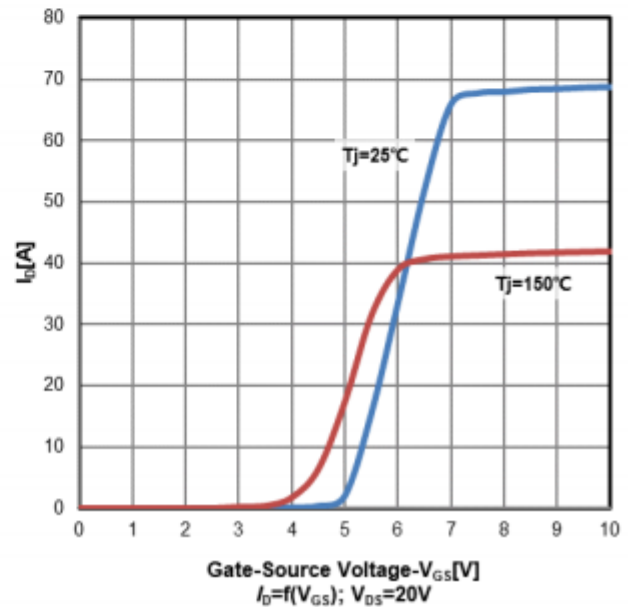
Drain current vs temperature



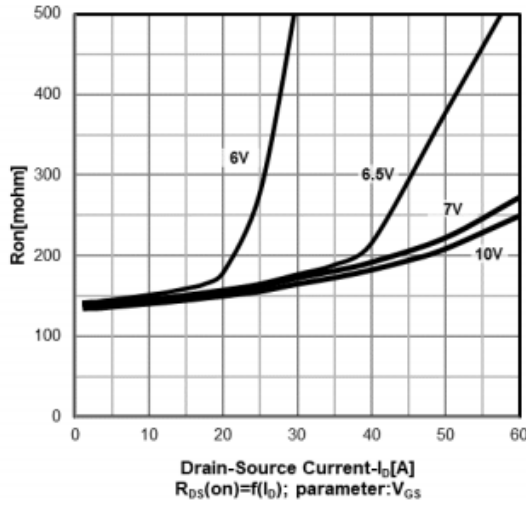
Typ. output characteristics  $T_J=25\text{ }^\circ\text{C}$



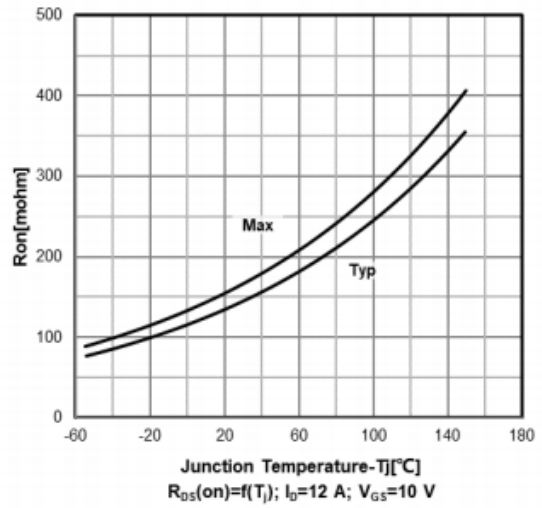
Typ. transfer characteristics



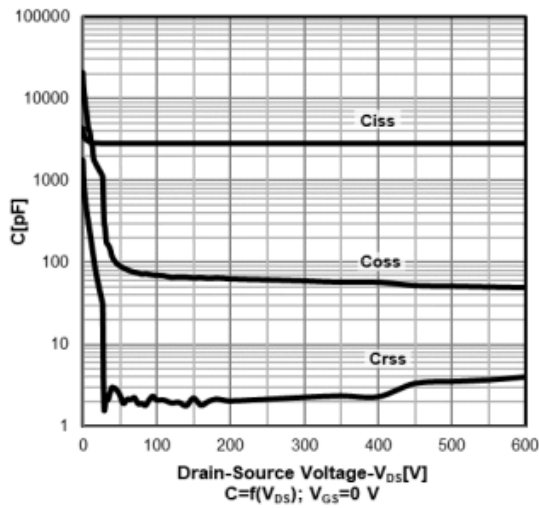
Typ. drain-source on-state resistance



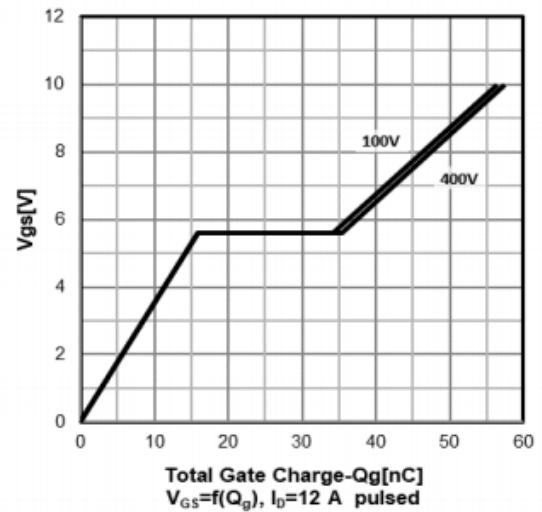
On resistance vs temperature



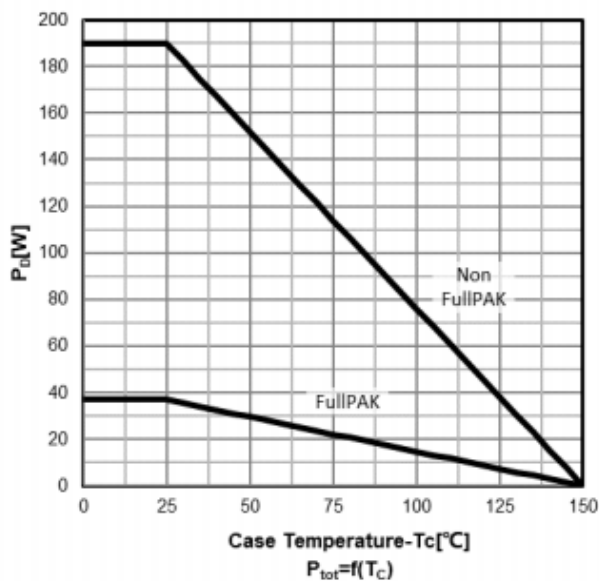
Typ. capacitances



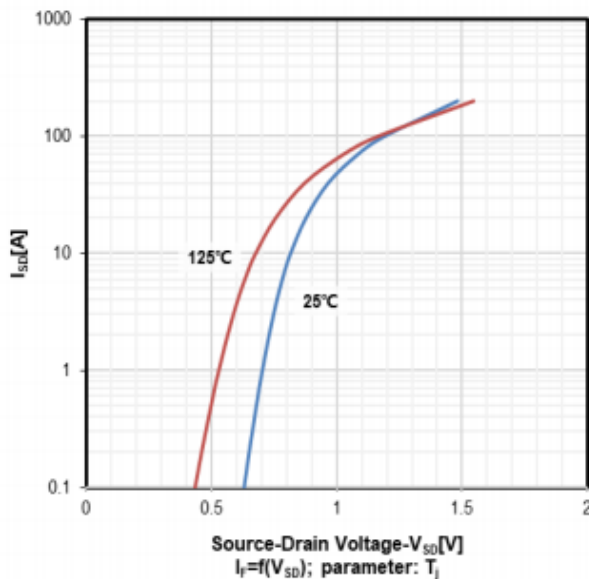
Typ. gate charge characteristics



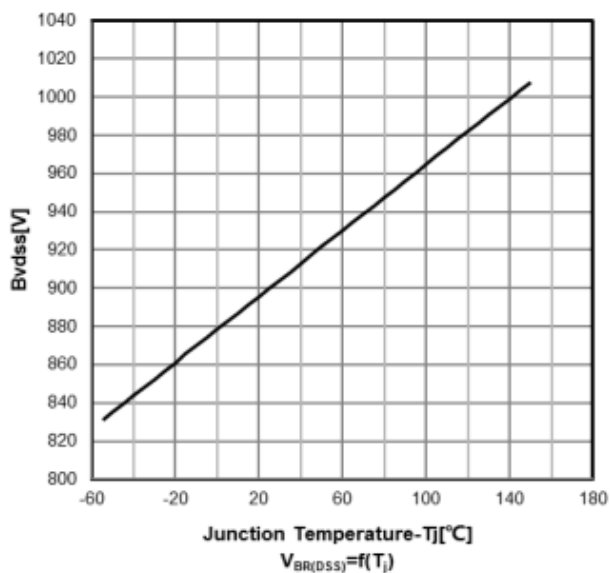
Power dissipation



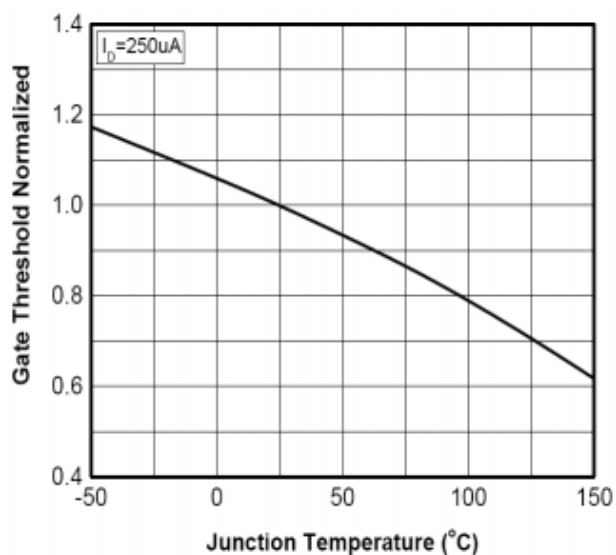
Forward characteristics of reverse diode



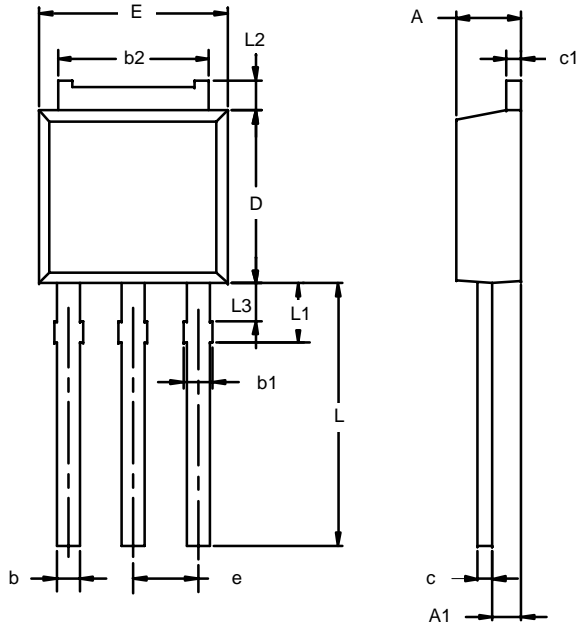
Drain-source breakdown voltage



Normalized  $V_{GS(th)}$  characteristics



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Note: Dimension L3 is for reference only.

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
<b>A</b>	2.21	2.38	0.087	0.094
<b>A1</b>	0.89	1.14	0.035	0.045
<b>b</b>	0.71	0.89	0.028	0.035
<b>b1</b>	0.76	1.14	0.030	0.045
<b>b2</b>	5.23	5.43	0.206	0.214
<b>c</b>	0.46	0.58	0.018	0.023
<b>c1</b>	0.46	0.58	0.018	0.023
<b>D</b>	5.97	6.22	0.235	0.245
<b>E</b>	6.48	6.73	0.255	0.265
<b>e</b>	2.28 BSC		0.090 BSC	
<b>L</b>	8.89	9.53	0.350	0.375
<b>L1</b>	1.91	2.28	0.075	0.090
<b>L2</b>	0.89	1.27	0.035	0.050
<b>L3</b>	1.15	1.52	0.045	0.060

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